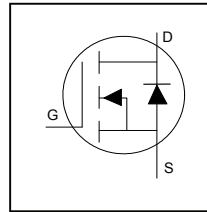


HEXFET® Power MOSFET

**Application**

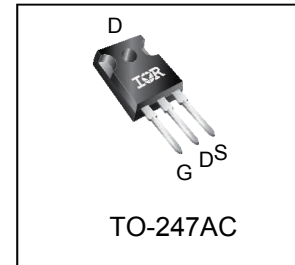
- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits



$V_{DSS}$	<b>250V</b>
$R_{DS(on)}$ typ.	<b>14.5mΩ</b>
	<b>17.5mΩ</b>
$I_D$	<b>93A</b>

**Benefits**

- Improved Gate, Avalanche and Dynamic  $dV/dt$  Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode  $dV/dt$  and  $dI/dt$  Capability
- Lead-Free, RoHS Compliant



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFP4768PbF	TO-247AC	Tube	25	IRFP4768PbF

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	93	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	66	
$I_{DM}$	Pulsed Drain Current ①	370	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	520	W
	Linear Derating Factor	3.4	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$dv/dt$	Peak Diode Recovery $dv/dt$ ③	24	V/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting Torque, 6-32 or M3 Screw	10 lbf·in (1.1 N·m)	

**Avalanche Characteristics**

$E_{AS}$ (Thermally limited)	Single Pulse Avalanche Energy ②	770	mJ
$I_{AR}$	Avalanche Current ①	See Fig. 14, 15, 22a, 22b	A
$E_{AR}$	Repetitive Avalanche Energy ①		mJ

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑦⑧	—	0.29	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat Greased Surface	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient	—	40	

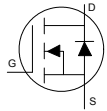
**Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	250	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.20	—	V/°C	Reference to $25^\circ\text{C}$ , $I_D = 5mA$ ①
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	14.5	17.5	mΩ	$V_{GS} = 10V, I_D = 56A$
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 250V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 250V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
$R_G$	Gate Resistance	—	0.71	—	Ω	

**Dynamic Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

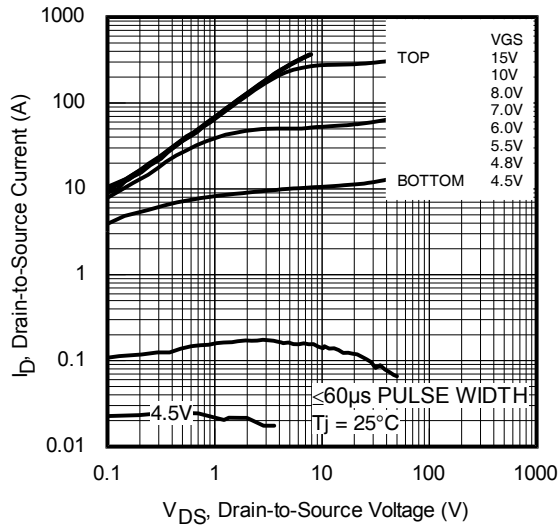
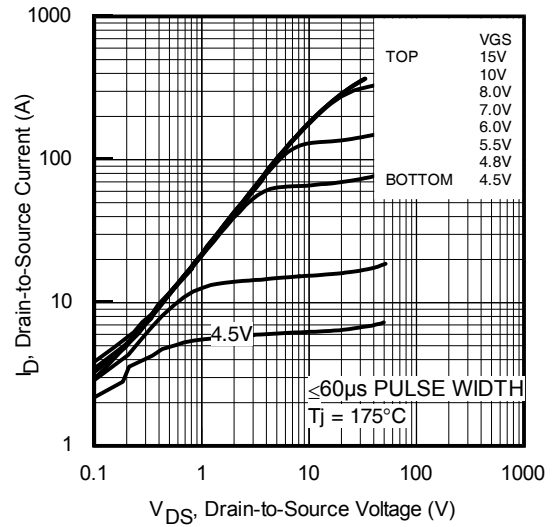
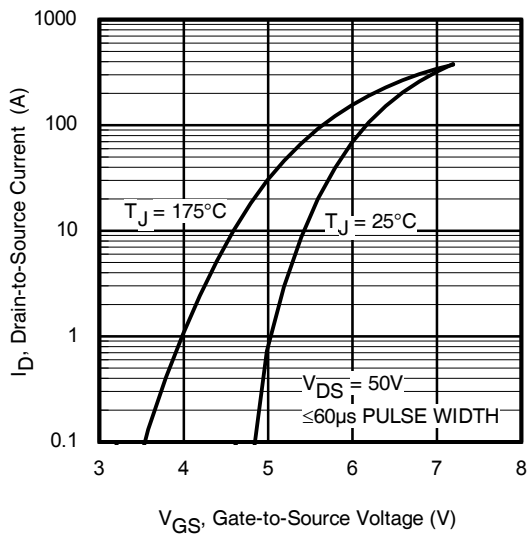
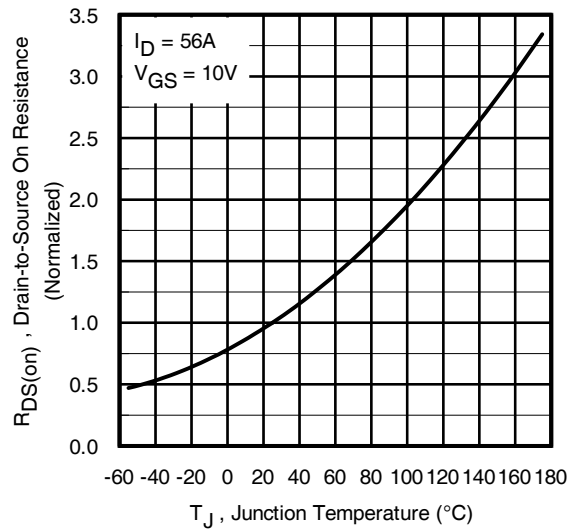
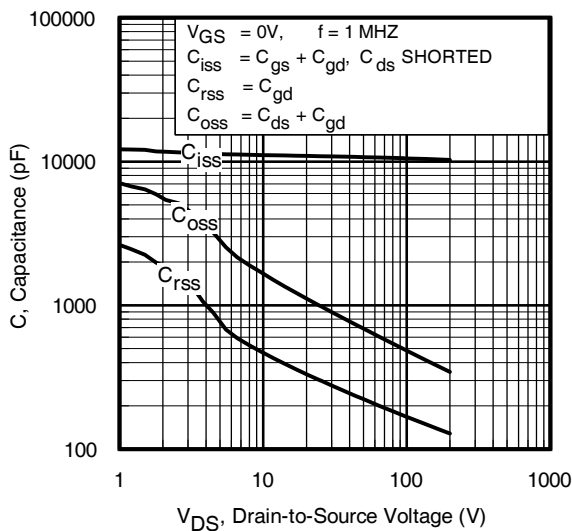
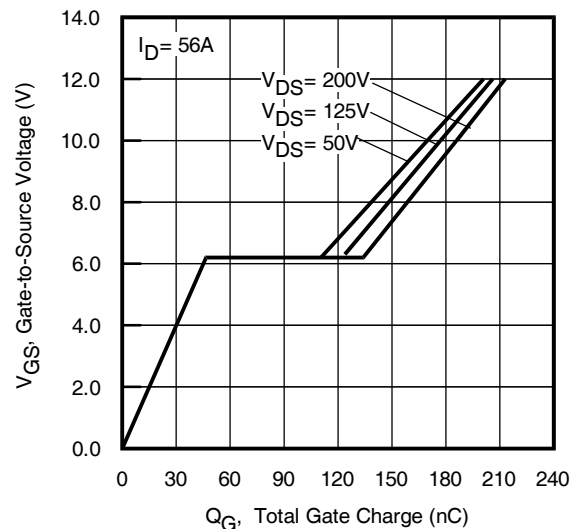
gfs	Forward Transconductance	100	—	—	S	$V_{DS} = 50V, I_D = 56A$
$Q_g$	Total Gate Charge	—	180	270	nC	$I_D = 56A$ $V_{DS} = 125V$ $V_{GS} = 10V$ ④
$Q_{gs}$	Gate-to-Source Charge	—	52	—		
$Q_{gd}$	Gate-to-Drain Charge	—	72	—		
$Q_{sync}$	Total Gate Charge Sync. ( $Q_g - Q_{gd}$ )	—	108	—		
$t_{d(on)}$	Turn-On Delay Time	—	36	—	ns	$V_{DD} = 163V$ $I_D = 56A$ $R_G = 1.0\Omega$ $V_{GS} = 10V$ ④
$t_r$	Rise Time	—	160	—		
$t_{d(off)}$	Turn-Off Delay Time	—	57	—		
$t_f$	Fall Time	—	110	—		
$C_{iss}$	Input Capacitance	—	10880	—	pF	$V_{GS} = 0V$ $V_{DS} = 50V$ $f = 1.0MHz$ , See Fig. 5
$C_{oss}$	Output Capacitance	—	700	—		
$C_{rss}$	Reverse Transfer Capacitance	—	210	—		
$C_{oss\ eff.(ER)}$	Effective Output Capacitance (Energy Related)	—	510	—		
$C_{oss\ eff.(TR)}$	Output Capacitance (Time Related)	—	830	—		

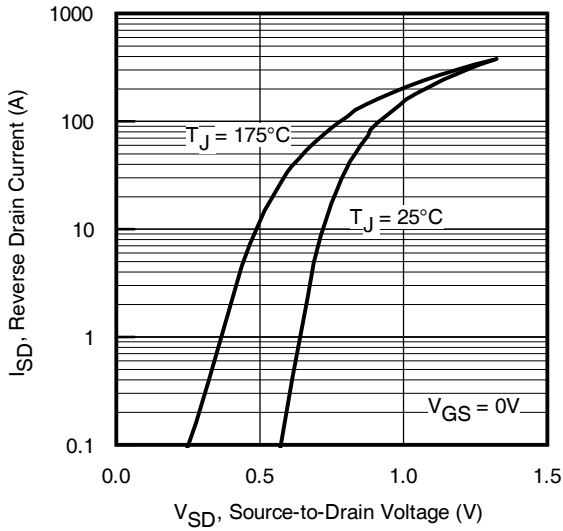
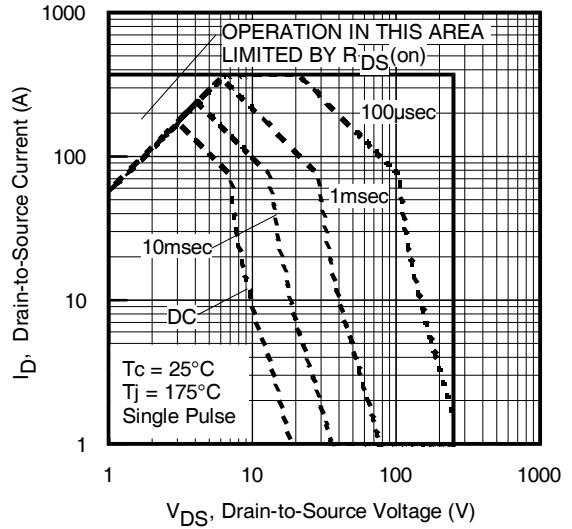
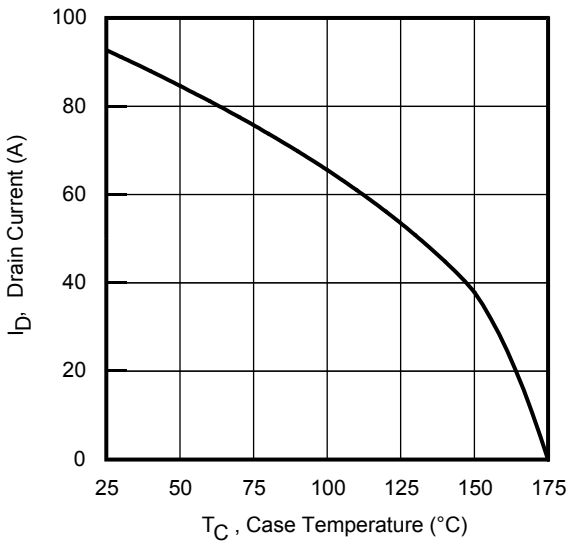
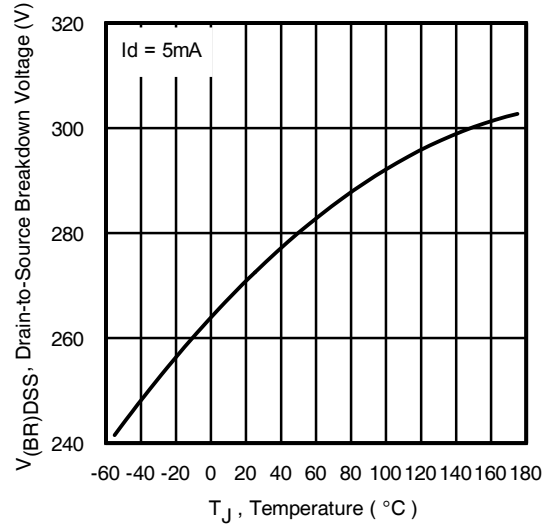
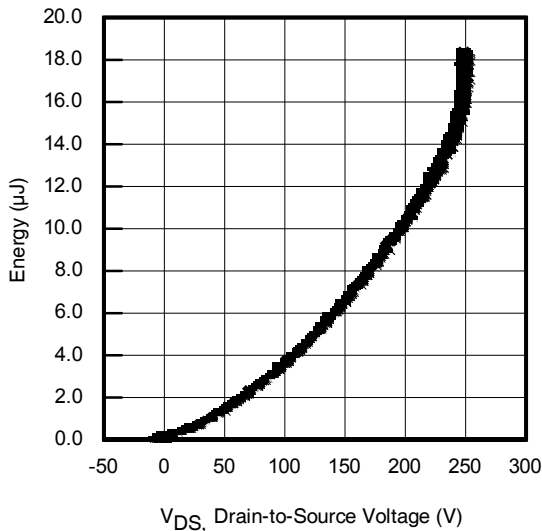
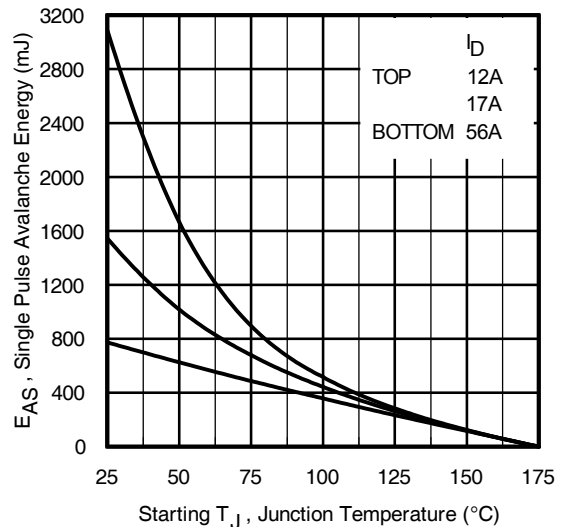
**Diode Characteristics**

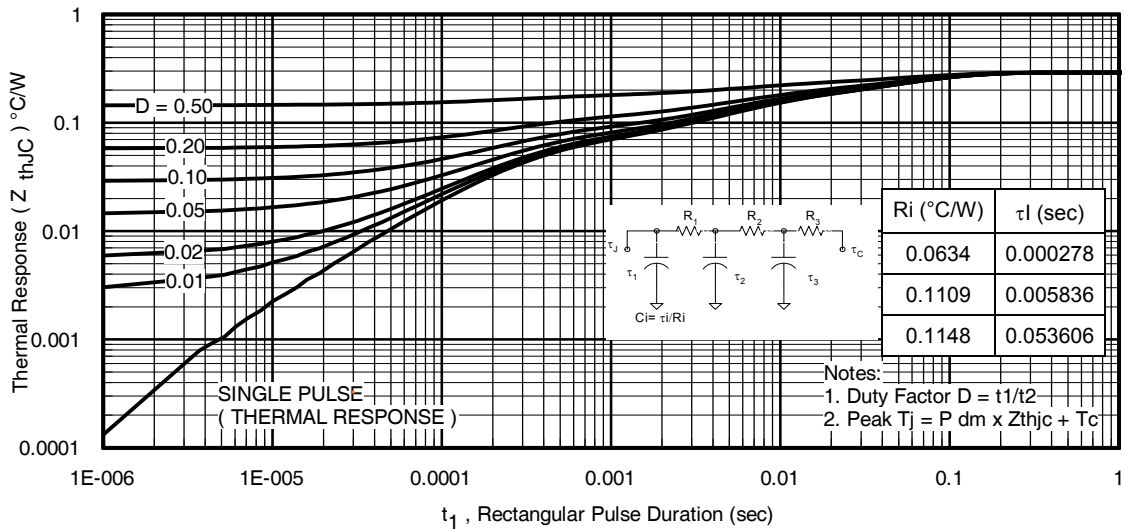
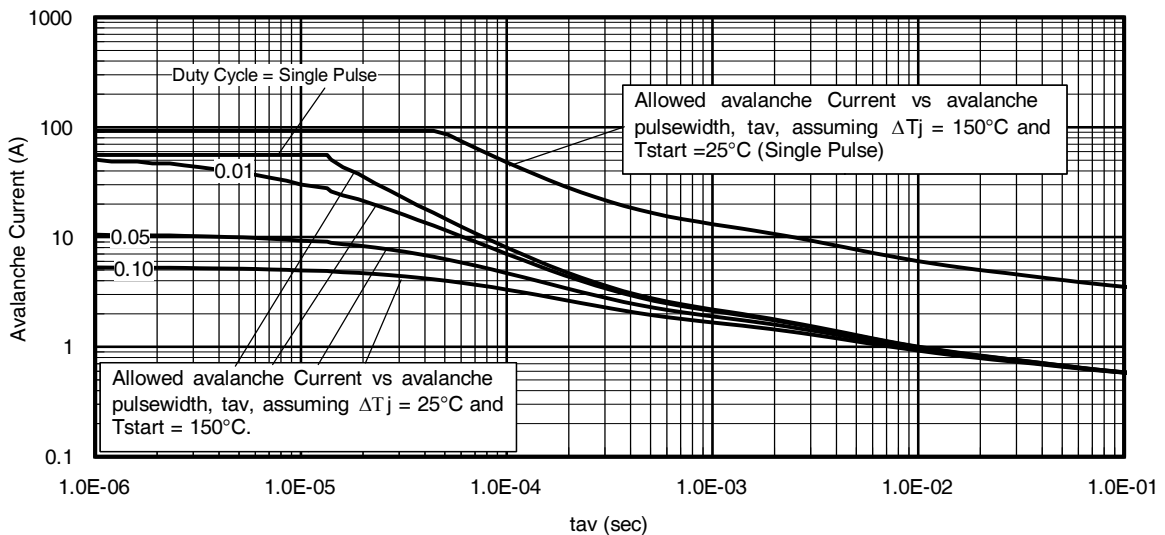
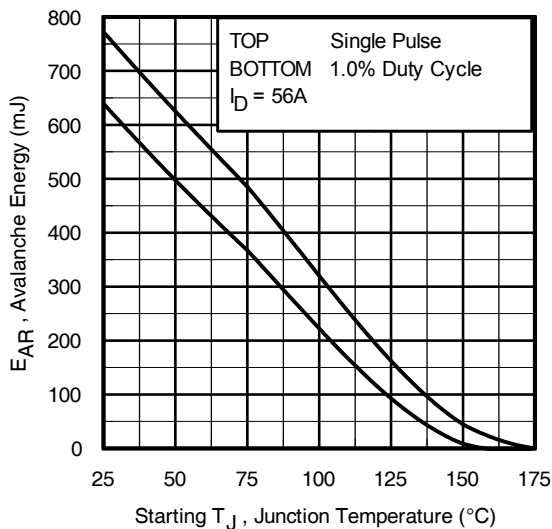
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	93	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	370		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 56A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	180	—	ns	$T_J = 25^\circ\text{C}$ $V_{DD} = 200V$ $T_J = 125^\circ\text{C}$ $I_F = 56A$ , $di/dt = 100A/\mu s$ ④
		—	200	—		
$Q_{rr}$	Reverse Recovery Charge	—	1480	—	nC	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$
		—	2260	—		
$I_{RRM}$	Reverse Recovery Current	—	16	—	A	$T_J = 25^\circ\text{C}$
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by  $T_{Jmax}$  starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.50mH$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 56A$ ,  $V_{GS} = 10V$ . Part not recommended for use above this value.
- ③  $I_{SD} \leq 56A$ ,  $di/dt \leq 950A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 175^\circ\text{C}$ .
- ④ Pulse width  $\leq 400\mu s$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{oss\ eff. (TR)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑥  $C_{oss\ eff. (ER)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑦  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$
- ⑧  $R_{\theta JC}$  value shown is at time zero.


**Fig 1. Typical Output Characteristics**

**Fig 2. Typical Output Characteristics**

**Fig 3. Typical Transfer Characteristics**

**Fig 4. Normalized On-Resistance vs. Temperature**

**Fig 5. Typical Capacitance vs. Drain-to-Source Voltage**

**Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage**


**Fig 7.** Typical Source-Drain Diode Forward Voltage

**Fig 8.** Maximum Safe Operating Area

**Fig 9.** Maximum Drain Current vs. Case Temperature

**Fig 10.** Drain-to-Source Breakdown Voltage

**Fig 11.** Typical  $C_{oss}$  Stored Energy

**Fig 12.** Maximum Avalanche Energy vs. Drain Current


**Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case**

**Fig 14. Typical Avalanche Current vs. Pulse**

**Notes on Repetitive Avalanche Curves , Figures 14, 15:  
(For further info, see AN-1005 at www.irf.com)**

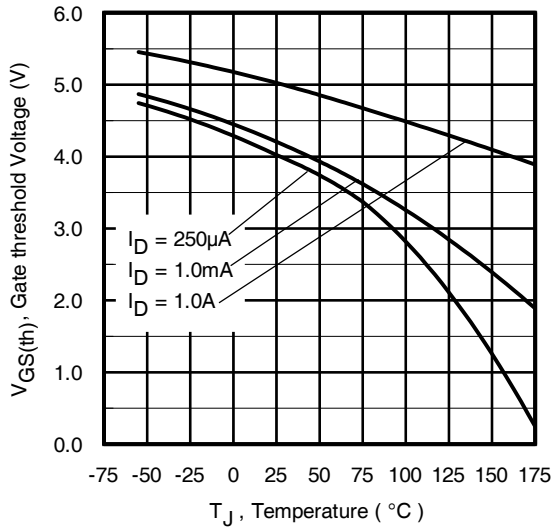
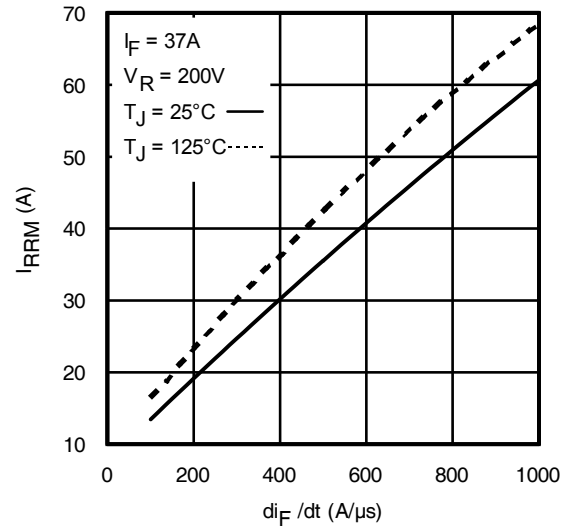
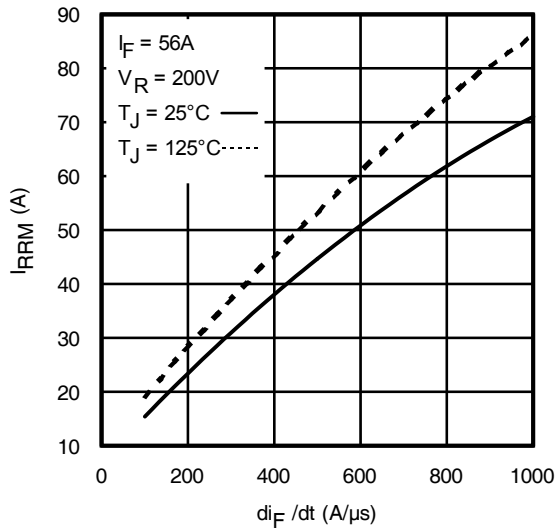
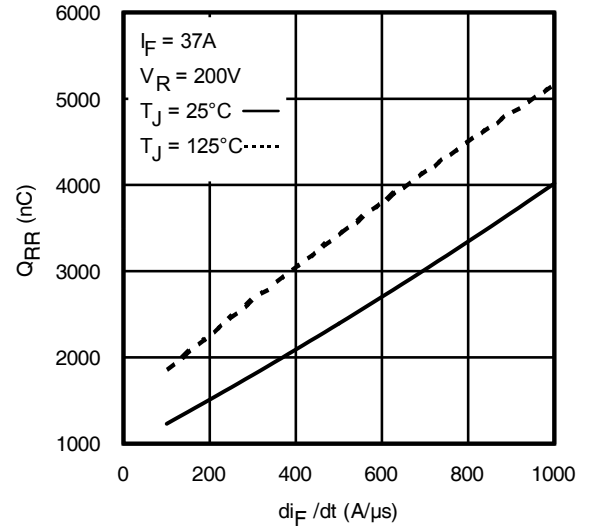
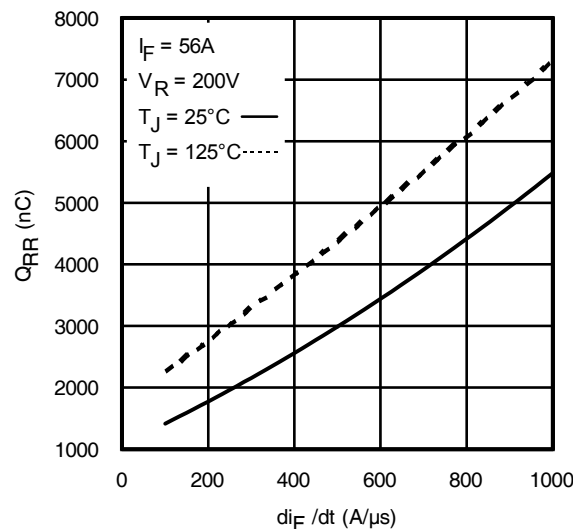
1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 22a,22b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 14, 15).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see Figures 13)

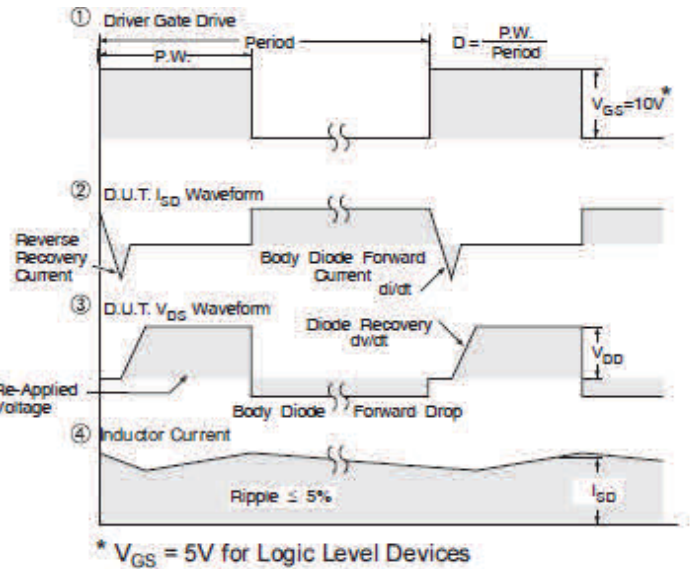
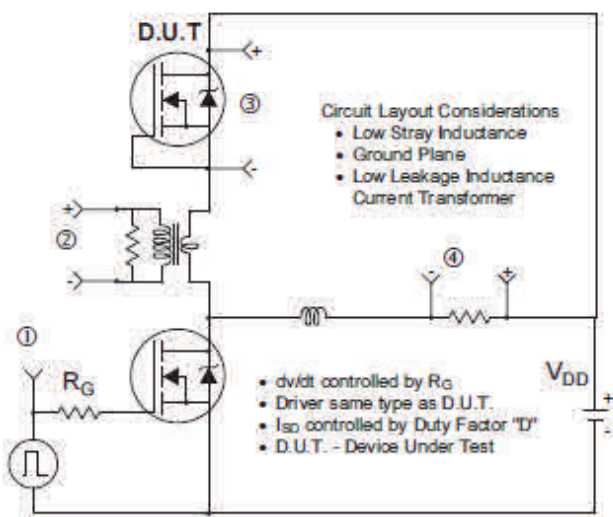
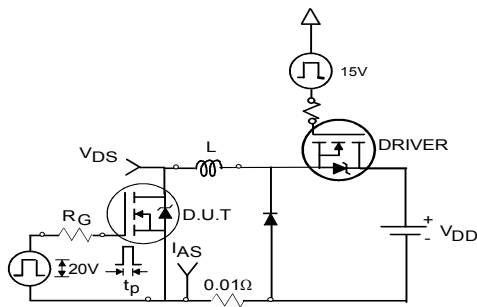
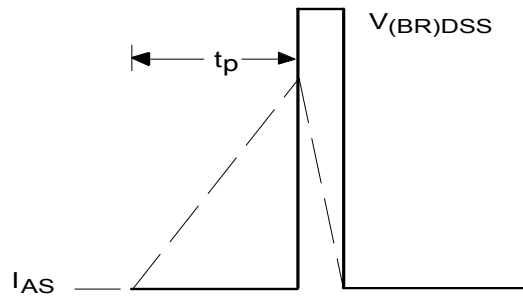
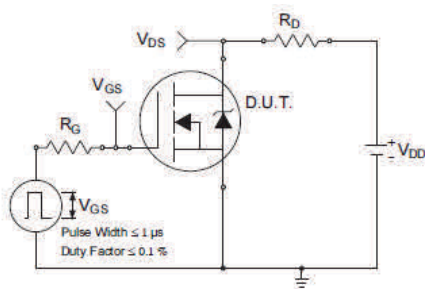
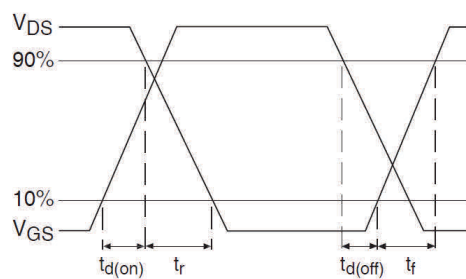
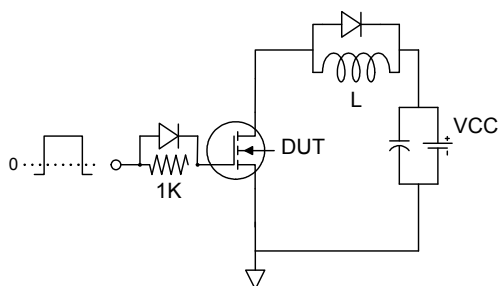
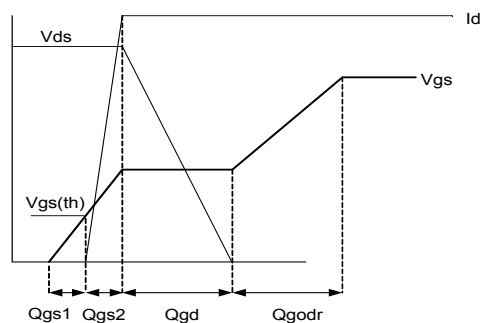
$$P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

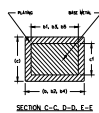
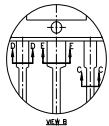
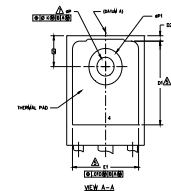
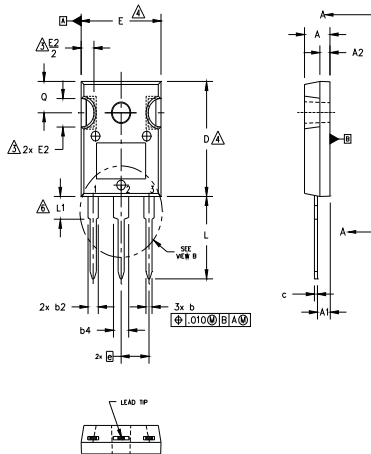
**Fig 15. Maximum Avalanche Energy vs. Temperature**


**Fig 16.** Threshold Voltage vs. Temperature

**Fig 17.** Typical Recovery Current vs.  $di_F/dt$ 

**Fig 18.** Typical Recovery Current vs.  $di_F/dt$ 

**Fig 19.** Typical Stored Charge vs.  $di_F/dt$ 

**Fig 20.** Typical Stored Charge vs.  $di_F/dt$


**Fig 21. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs**

**Fig 22a. Unclamped Inductive Test Circuit**

**Fig 22b. Unclamped Inductive Waveforms**

**Fig 23a. Switching Time Test Circuit**

**Fig 23b. Switching Time Waveforms**

**Fig 24a. Gate Charge Test Circuit**

**Fig 24b. Gate Charge Waveform**

## TO-247AC Package Outline

Dimensions are shown in millimeters (inches)


**NOTES:**

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC .

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	-	13.08	-	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	-	13.46	-	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øk	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
ØP1	.140	.144	3.56	3.66	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

**LEAD ASSIGNMENTS**
**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

**DIODES**

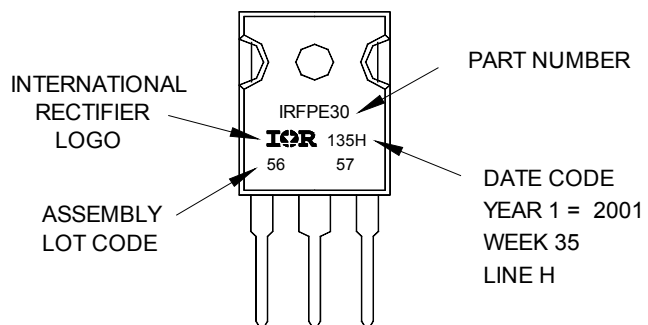
- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

## TO-247AC Part Marking Information

Notes: This part marking information applies to devices produced after 02/26/2001

EXAMPLE: THIS IS AN IRFPE30  
WITH ASSEMBLY  
LOT CODE 5657  
ASSEMBLED ON WW 35, 2001  
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position  
indicates "Lead-Free"



TO-247AC package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>



**Qualification Information**

<b>Qualification Level</b>	Industrial (per JEDEC JESD47F) †	
<b>Moisture Sensitivity Level</b>	TO-247AC	N/A
<b>RoHS Compliant</b>	Yes	

† Applicable version of JEDEC standard at the time of product release.

**Revision History**

<b>Date</b>	<b>Comments</b>
12/12/2016	<ul style="list-style-type: none"> <li>• Changed datasheet with Infineon logo-all pages</li> <li>• Corrected error on figure 9 on page 4.</li> <li>• Added disclaimer on last page.</li> </ul>

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